



YANGZHOU POSITIONING TECH. CO., LTD

NPN SILICON TRANSISTOR

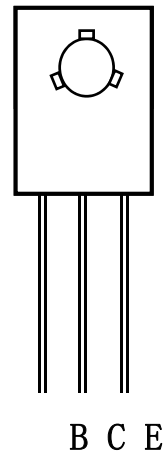
PST13003DL

◆ Energy-saving Lamp Rectifier

◆ Absolute Maximum Ratings (Tc=25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	VCBO	350	V
Collector-Emitter Voltage	VCEO	220	V
Emitter-Base Voltage	VEBO	9	V
Collector Current	IC	3	A
Total Power Dissipation	PC	25	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~150	°C

T0-126



◆ Electronic Characteristics (Tc=25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector-Base Voltage	VCBO	Ic=1mA Ie=0	350		V
Collector-Emitter Voltage	VCEO	Ic=1mA Ib=0	220		V
Emitter-Base Voltage	VEBO	Ie=1mA Ic=0	9		V
Collector-Base Cutoff Current	ICBO	Vcb=350v Ie=0		10	UA
Collector-Emitter Cutoff Current	ICEO	Vce=220v Ib=0		10	UA
Emitter-Base Cutoff Current	IEBO	Veb=9v Ic=0		10	UA
Collector-Emitter Saturation Voltage	Vce(sat)	Ic=0.5A Ib=0.1A		0.9	V
Base-Emitter Saturation Voltage	Vbe(sat)	Ic=0.5A Ib=0.1A		1.5	V
DC Current Gain	Hfe	VCE=5v IC=0.2A	20	25	
Diode Forward Voltage	Vf	IF=1.0A		2	V
Storage Time	ts	Ic=0.25A (UI9602)	1.5	2.5	us